

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent No 7,056,833 B2
Patent Issue Date June 6, 2006
Application Serial No. 10/669,671
Filing Date September 23, 2003
Assignee Micron Technology, Inc.
Inventorship Rueger et al.
Attorney's Docket No. MI22-2145
Title: Methods of Filling Gaps and Methods of Depositing Materials Using High
Density Plasma Chemical Vapor Deposition

**REQUEST FOR CERTIFICATE OF CORRECTION OF PATENT FOR
APPLICANT MISTAKES and PTO MISTAKES (37 C.F.R. §§ 1.322(a) and 1.323)**

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450
ATTN: Decision and Certificate of Correction
Branch of the Patent Issue Division

From: Jennifer J. Taylor, Ph.D. (Tel. 509-624-4276; Fax 509-838-3424)
Wells St. John P.S.
601 W. First Avenue, Suite 1300
Spokane, WA 99201-3828

Sir:

It is hereby requested that a Certificate of Correction be issued with respect to Patent No. 7,056,833 B2, granted June 6, 2006, in accordance with the Certificate of Correction form attached hereto.

It is noted that errors appear in this patent of a typographical nature of character, as more fully described below. The errors occurred in good faith. Correction thereof does not involve such changes in the patent as would constitute new matter or would require re-examination.

Other errors listed on the Certificate of Correction form were apparently incurred through the fault of the PTO as will be disclosed by the records of files in the Office.

Attached hereto is Form PTO-1050 that is suitable for printing.

The exact page and line number where the errors occur in the application file are:

Paragraph 7, Line 4

Paragraph 27, Lines 1, 9 and 10

Paragraph 32, Line 2

Paragraph 34, Line 4

Paragraph 35, Line 5

Paragraph 42, Line 13

Deposit Account 23-0925 is to be charged in the amount of \$100.00, as required by 37 CFR 1.20(a).

Dated: March 23, 2007

Respectfully submitted,
By: Jennifer J. Taylor
Jennifer J. Taylor Ph.D.
Reg. No. 48,711

UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO. : 7,056,833 B2

DATED : June 6, 2006

INVENTOR(S) : Rueger et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 1, Line 64 – Replace “DT; T₂” with --DT, T₂--.

Column 4, Line 1 – replace “oxide layer 14” with --oxide layer 104--.

Column 4, Line 12 – Replace “deposition of can” with --deposition can--.

Column 4, Line 44 – Replace “changed or adjusting” with --changed or adjusted--.

Column 4, Line 58 – Replace “is substitute for” with --is substituted for--.

Column 5, Line 25 – Replace “F, As Ge” with --F, As, Ge--.

Column 5, Line 42 – Delete “SiCl₂R₂,” after “SiCl₂R₂,”.

Column 6, Line 65 – Replace “narrow a few” with --narrow as a few--.

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Patent No. 7,056,833 B2